TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

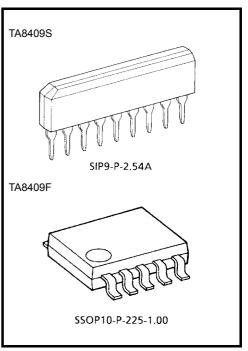
# TA8409S,TA8409F

#### Bridge Driver

TA8409S and TA8409F are bridge driver with output voltage control.

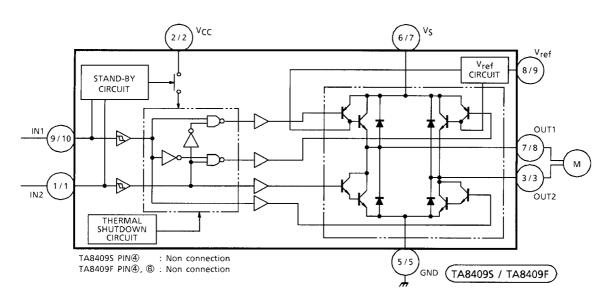
### Features

- Modes available (CW/CCW/STOP/BRAKE)
- Output current up to 0.4 A (AVE) and 1.0 A (PEAK)
- Wide range of operating voltage V<sub>CC</sub> (opr.) = 4.5 to 20 V V<sub>S</sub> (opr.) = 0 to 20 V V<sub>ref</sub> (opr.) = 0 to 20 V (V<sub>ref</sub> ≤ V<sub>S</sub>)
- Built-in thermal shutdown
- Standby mode available (STOP MODE)
- Hysteresis for all inputs.



#### Weight

SIP9-P-2.54A: 0.92 g (typ.) SSOP10-P-225-1.00: 0.09 g (typ.)



### **Block Diagram**

### **Pin Function**

#### TA8409S

Pin No.	Symbol	Functional Description			
1	IN2	Input terminal			
2	V <sub>CC</sub>	Supply voltage terminal for logic			
3	OUT2	Output terminal			
4	NC	Non connection			
5	GND	GND terminal			
6	VS	Supply voltage terminal for motor driver			
7	OUT1	Output terminal			
8	V <sub>ref</sub>	Reference voltage terminal for control circuit			
9	IN1	Input terminal			

#### TA8409F

Pin No.	Symbol	Functional Description			
1	IN2	Input terminal			
2	V <sub>CC</sub>	Supply voltage terminal for logic			
3	OUT2	Output terminal			
4	NC	Non connection			
5	GND	GND terminal			
6	NC	Non connection			
7	VS	Supply voltage terminal for motor driver			
8	OUT1	Output terminal			
9	V <sub>ref</sub>	Reference voltage terminal for control circuit.			
10	IN1	Input terminal			

### Function

Input		Out	Mode	
IN 1	IN 2	OUT1	OUT2	MB
0	0	8	8	STOP
1	0	Н	L	CW/CCW
0	1	L	Н	CCW/CW
1	1	L	L	BRAKE

∞: High impedance

Note: Inputs are all high active type.

## Maximum Ratings (Ta = 25°C)

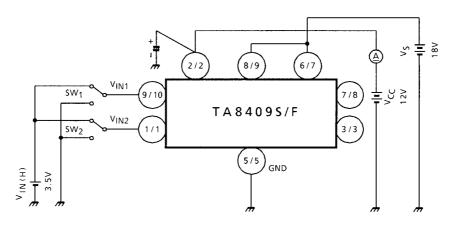
Characteristics		Symbol	Rating	Unit	
Supply voltage		V <sub>CC</sub>	25	V	
Motor drive voltage		VS	25	V	
Reference voltage		V <sub>ref</sub>	25	V	
Output current	PEAK	I <sub>O (PEAK)</sub>	1.0	A	
Output current	AVE.	I <sub>O (AVE.)</sub>	0.4		
Power dissipation	TA8409F	PD	0.735 (Note)	W	
	TA8409S	-0	0.95		
Operating temperature		T <sub>opr</sub>	-30 to 75	°C	
Storage temperature		T <sub>stg</sub>	-55 to 150	°C	

Note: This rating is obtained by mounting on  $50 \times 50 \times 1.6$  mm PCB that occupied above 30% of copper area.

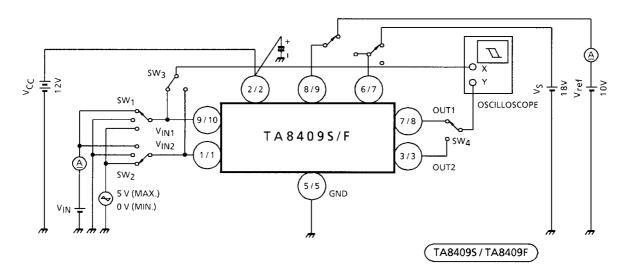
### Electrical Characteristics (Ta = 25°C, V<sub>CC</sub> = 12 V, V<sub>S</sub> = 18 V)

Characteristics		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Supply current		I <sub>CC1</sub>	1	Output OFF, CW/CCW mode - 10.		10.0	15.0	mA	
		I <sub>CC2</sub>	1	Output OFF, STOP mode - 0		0	50	μA	
		I <sub>CC3</sub>	1	Output OFF, BREAK mode	—	6.5	10.0	) mA	
Input operating	1 (High)	V <sub>IN 1</sub>	2	T <sub>j</sub> = 25°C IN1, 2	3.5	_	5.5	V	
voltage	2 (Low)	V <sub>IN 2</sub>	2	T <sub>j</sub> = 25°C IN1, 2	GND	—	0.8	V	
Input current		I <sub>IN</sub>	2	Sink mode, V <sub>IN</sub> = 3.5 V	—	3	10	μA	
Input hysteresis voltage	9	$\Delta V_T$	2	—	—	0.7	—	V	
	Upper side	VSAT U-1	3	$V_{ref} = V_S, V_{OUT} - V_S$ measure I <sub>O</sub> = 0.2 A, CW/CCW mode	_	0.9	1.2	V	
	Lower side	V <sub>SAT L-1</sub>	3	$V_{ref} = V_S, V_{OUT}$ -GND measure I <sub>O</sub> = 0.2 A, CW/CCW mode	_	0.8	1.2		
Saturation voltage	Upper side	VSAT U-2	3	$V_{ref} = V_S, V_{OUT} - V_S$ measure I <sub>O</sub> = 0.4 A, CW/CCW mode	_	1.0	1.35		
	Lower side	V <sub>SATL-2</sub>	3	$V_{ref} = V_S, V_{OUT}$ -GND measure $I_O = 0.4 A, CW/CCW$ mode	_	0.9	1.35		
Output voltage		VSAT U-1'	3	$V_{ref}$ = 10 V, $V_{OUT}$ -GND measure $I_O$ = 0.2 A	10.4	11.2	12.2	V	
		VSAT U-2'	3	V <sub>ref</sub> = 10 V, V <sub>OUT</sub> -GND measure I <sub>O</sub> = 0.4 A	_	10.9	_	V	
Output transistor leakage current	Upper side	I <sub>LU</sub>	4	V <sub>L</sub> = 25 V	_	_	50		
	Lower side	ارر	4	V <sub>L</sub> = 25 V	_	_	50	μA	
Diode forward voltage	Upper side	V <sub>FU-1</sub>	5	I <sub>F</sub> = 0.4 A	_	1.5	—	v	
Dioue iorward vollage	Lower side	V <sub>FL-1</sub>	5	I <sub>F</sub> = 0.4 A	—	0.9	—	v	
Reference current		I <sub>ref</sub>	2	V <sub>ref</sub> = 10 V, source mode	_	20	40	μA	

Test Circuit 1 Icc1, Icc2, Icc3

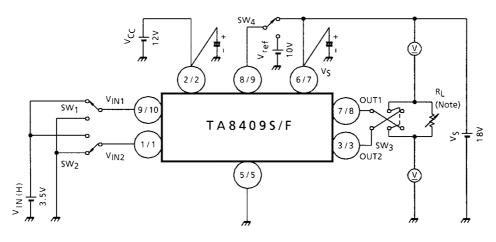


Test Circuit 2  $V_{IN1}, V_{IN2}, I_{IN}, \Delta V_T, I_{ref}$ 



# Test Circuit 3

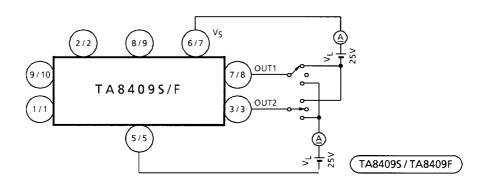
VSAT U-1, 2, VSAT L-1, 2, VSAT U-1', 2'



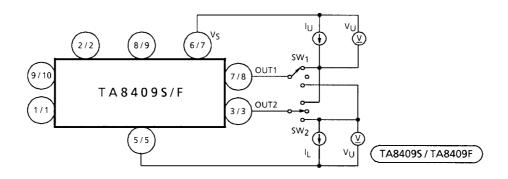
Note: Calibrate I<sub>OUT</sub> to 0.2/0.4 A by R<sub>L</sub>.

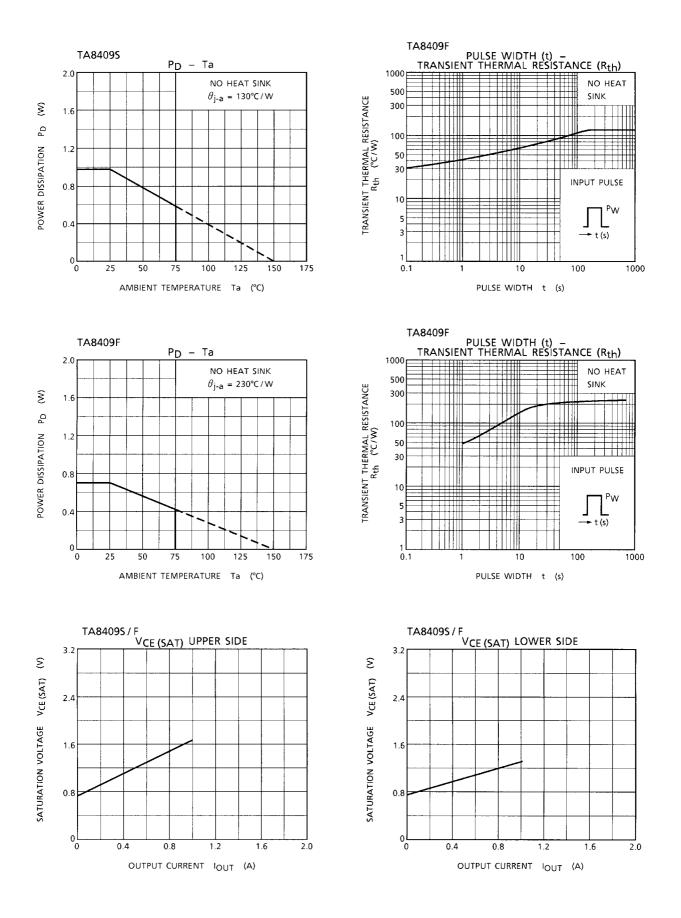
### **Test Circuit 4**

I<sub>L U, L</sub>



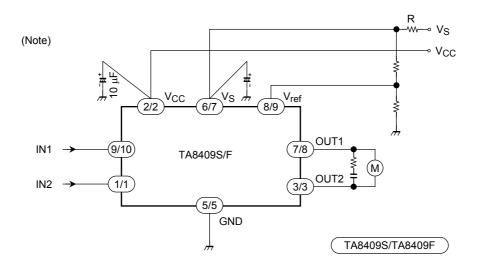
#### Test Circuit 5 V<sub>F U-1, 2</sub>, V<sub>F L-1, 2</sub>





# Application Circuit

roshiba

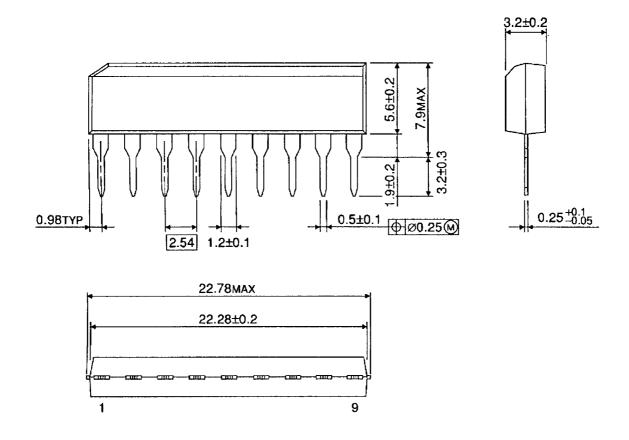


- Note 1: Attach a bypass capacitor to the Vs pin as required.
- Note 2: Utmost care is necessary in the design of the output line, V<sub>S</sub>, V<sub>CC</sub> and GND line since IC may be destroyed due to short-circuit between outputs, to supply fault, or to ground. Also note in mind that mounting the IC in the reverse orientation may also cause a breakdown.
- Note 3: Switching the inputs may allow a pass-through current to flow. Keep the IC device in the STOP mode (for at least 100 µs) during the switching. Alternatively, insert a current limiting resistor R.
- Note 4: Use a current limiting resistor R or fuse for overcurrent protection.
- Note 5: When turning on the power for the IC device, apply VS after V<sub>CC</sub> (or V<sub>CC</sub> and V<sub>S</sub> simultaneously). When shutting off the power, drop V<sub>S</sub> before V<sub>CC</sub> (or Vs and V<sub>CC</sub> simultaneously). When turning on the power (V<sub>CC</sub>), keep both the inputs (IN1 and IN2) on a low level.

# Package Dimensions

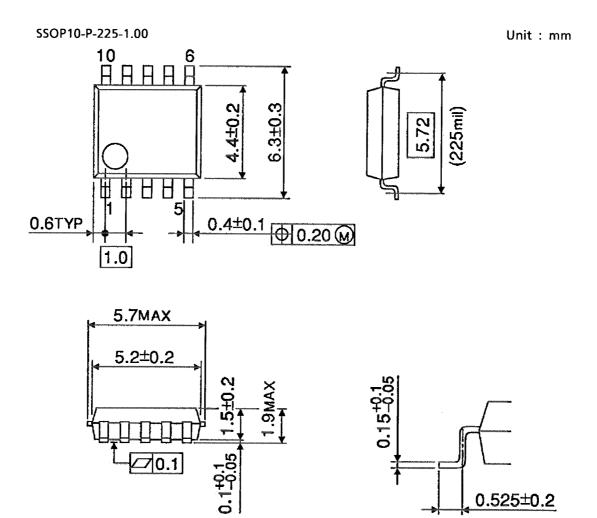
SIP9-P-2.54A

Unit : mm



Weight: 0.92 g (typ.)

### Package Dimensions



Weight: 0.09 g (typ.)

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